	L#	Hits	Search Text	DBs	Time Stamp
1	L1	60487	(cold ADJ cathode) OR (field ADJ (emission OR emit\$4))	US- PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWE NT; IBM_TD B	2007/10/11 16:55
2	L2	3649	cathode WITH ((plural\$3 OR multi\$3 OR several OR many OR two OR second) ADJ3 (insulat\$3 OR glass OR silicate OR (silicon ADJ oxide) OR ("SiO.sub.2") OR passivation))	US- PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWE NT; IBM_TD B	2007/10/11 16:56
3	L3	770	1 AND 2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWE NT; IBM_TD B	2007/10/11 16:56
4	L4	26033	gate WITH ((plural\$3 OR multi\$3 OR several OR many OR two OR second) ADJ3 (insulat\$3 OR glass OR silicate OR (silicon ADJ oxide) OR ("SiO.sub.2") OR passivation))	US- PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWE NT; IBM_TD B	2007/10/11 16:56

	L#	Hits	Search Text	DBs	Time Stamp
5	L5	344	3 AND 4	US- PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWE NT; IBM_TD B	2007/10/11 16:56
6	L6	292116	thickness WITH (insulat\$3 OR glass OR silicate OR (silicon ADJ oxide) OR ("SiO.sub.2") OR passivation)		2007/10/11 16:57
7	L7	186	5 AND 6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWE NT; IBM_TD B	2007/10/11 16:57